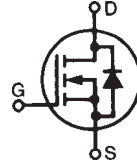


# TrenchT2™ HiperFET™ IXFA230N075T2-7

## Power MOSFET

N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Rectifier

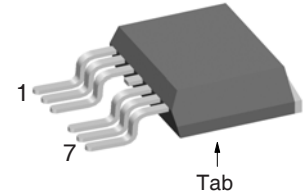


$$V_{DSS} = 75V$$

$$I_{D25} = 230A$$

$$R_{DS(on)} \leq 4.2m\Omega$$

TO-263 (7-lead)



Pins: 1 - Gate  
2, 3 - Source  
5, 6, 7 - Source  
Tab (8) - Drain

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ C$ to $175^\circ C$	75	V
$V_{DGR}$	$T_J = 25^\circ C$ to $175^\circ C$ , $R_{GS} = 1M\Omega$	75	V
$V_{GSM}$	Transient	$\pm 20$	V
$I_{D25}$	$T_C = 25^\circ C$ (Chip Capability)	230	A
$I_{LRMS}$	Lead Current Limit, RMS	160	A
$I_{DM}$	$T_C = 25^\circ C$ , pulse width limited by $T_{JM}$	700	A
$I_A$	$T_C = 25^\circ C$	115	A
$E_{AS}$	$T_C = 25^\circ C$	850	mJ
$P_D$	$T_C = 25^\circ C$	480	W
$T_J$		-55 ... +175	$^\circ C$
$T_{JM}$		175	$^\circ C$
$T_{stg}$		-55 ... +175	$^\circ C$
$T_L$	1.6mm (0.062in.) from case for 10s	300	$^\circ C$
$T_{sold}$	Plastic body for 10 seconds	260	$^\circ C$
Weight	TO-263	3	g

### Features

- International Standard Package
- $175^\circ C$  Operating Temperature
- High Current Handling Capability
- Avalanche Rated
- Fast Intrinsic Rectifier
- Low  $R_{DS(on)}$

### Advantages

- Easy to Mount
- Space Savings
- High Power Density

### Applications

- Automotive
  - Motor Drives
  - 12V Power Bus
  - ABS Systems
- DC/DC Converters and Off-Line UPS
- Primary- Side Switch
- High Current Switching Applications

Symbol	Test Conditions ( $T_J = 25^\circ C$ Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0V$ , $I_D = 250\mu A$	75		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 1mA$	2.0		4.0 V
$I_{GSS}$	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$			$\pm 200$ nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ , $V_{GS} = 0V$			25 $\mu A$
	$T_J = 150^\circ C$			250 $\mu A$
$R_{DS(on)}$	$V_{GS} = 10V$ , $I_D = 50A$ , Notes 1 & 2			4.2 m $\Omega$

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 10\text{V}$ , $I_D = 60\text{A}$ , Note 1	50	85	S
$C_{iss}$	$V_{GS} = 0\text{V}$ , $V_{DS} = 25\text{V}$ , $f = 1\text{MHz}$		10.5	nF
$C_{oss}$			1165	pF
$C_{rss}$			125	pF
$t_{d(on)}$	<b>Resistive Switching Times</b> $V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$ $R_G = 2\Omega$ (External)		23	ns
$t_r$			18	ns
$t_{d(off)}$			33	ns
$t_f$			15	ns
$Q_{g(on)}$	$V_{GS} = 10\text{V}$ , $V_{DS} = 0.5 \cdot V_{DSS}$ , $I_D = 0.5 \cdot I_{D25}$		178	nC
$Q_{gs}$			53	nC
$Q_{gd}$			41	nC
$R_{thJC}$				0.31 $^\circ\text{C/W}$

### Source-Drain Diode

Symbol	Test Conditions ( $T_J = 25^\circ\text{C}$ , Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{V}$			230 A
$I_{SM}$	Repetitive, Pulse width limited by $T_{JM}$			900 A
$V_{SD}$	$I_F = 100\text{A}$ , $V_{GS} = 0\text{V}$ , Note 1			1.3 V
$t_{rr}$	$I_F = 115\text{A}$ , $V_{GS} = 0\text{V}$ $-di/dt = 100\text{A}/\mu\text{s}$ $V_R = 37\text{V}$		59	ns
$I_{RM}$			3.6	A
$Q_{RM}$			106	nC

- Notes: 1. Pulse test,  $t \leq 300\mu\text{s}$ ; duty cycle,  $d \leq 2\%$ .  
 2. On through-hole packages,  $R_{DS(on)}$  Kelvin test contact location must be 5mm or less from the package body.

**TO-263 (7-lead) (IXFA..7) Outline**

Pins: 1 - Gate  
 2, 3 - Source  
 4 - Drain  
 5,6,7 - Source  
 Tab (8) - Drain

SYM	INCHES		MILLIMETER	
	MIN	MAX	MIN	MAX
A	.170	.185	4.30	4.70
A1	.085	.104	2.15	2.65
b	.026	.035	0.65	0.90
c	.016	.024	0.40	0.60
c2	.049	.055	1.25	1.40
D	.355	.370	9.00	9.40
D1	.272	.280	6.90	7.10
E	.386	.402	9.80	10.20
E1	.311	.319	7.90	8.10
e	.050 BSC		1.27 BSC	
L	.591	.614	15.00	15.60
L1	.091	.110	2.30	2.80
L2	.039	.059	1.00	1.50
L3	.000	.059	0.00	1.50

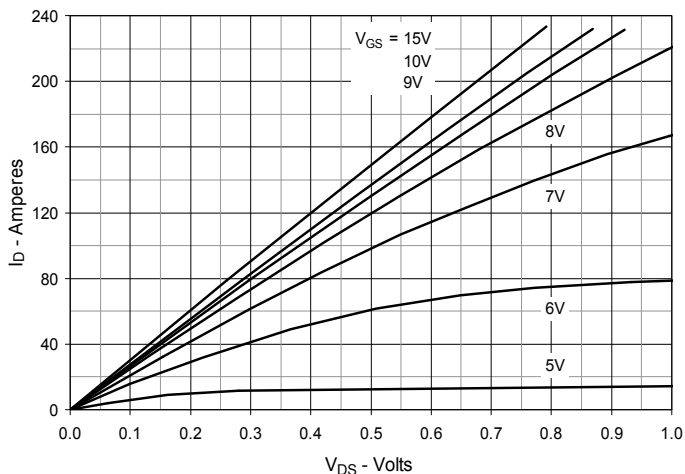
### ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

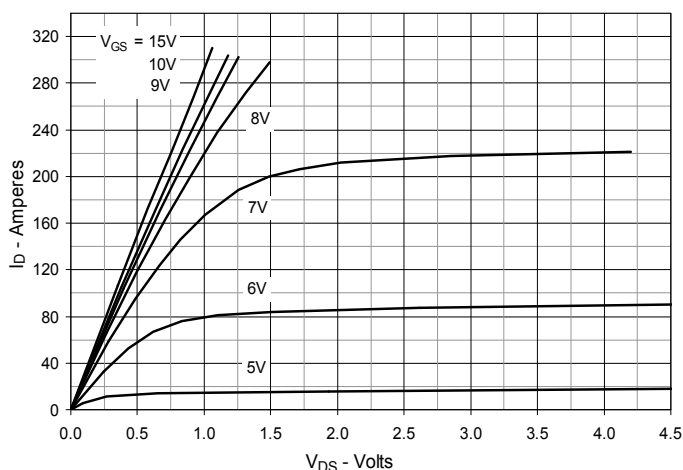
IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,850,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

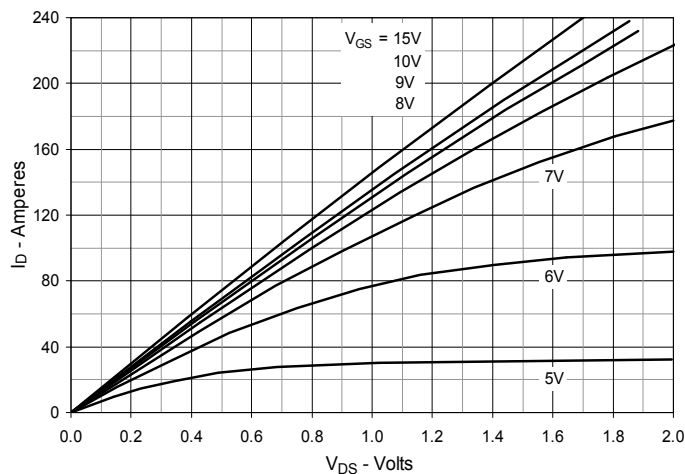
**Fig. 1. Output Characteristics @  $T_J = 25^\circ\text{C}$**



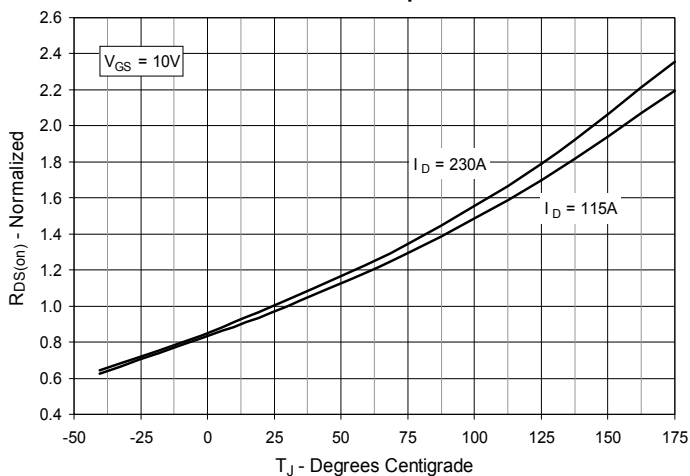
**Fig. 2. Extended Output Characteristics @  $T_J = 25^\circ\text{C}$**



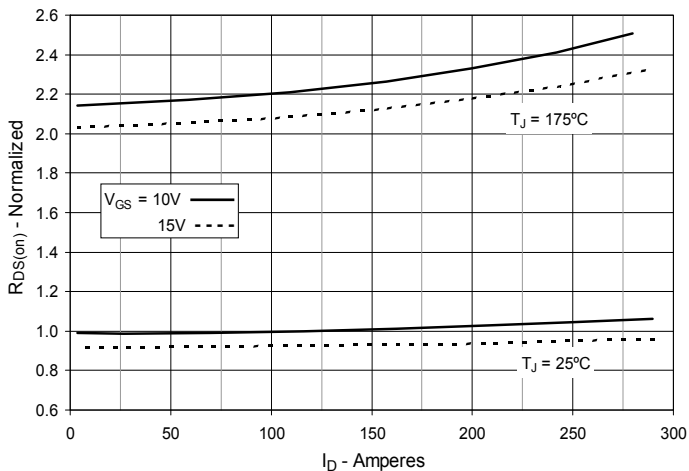
**Fig. 3. Output Characteristics @  $T_J = 150^\circ\text{C}$**



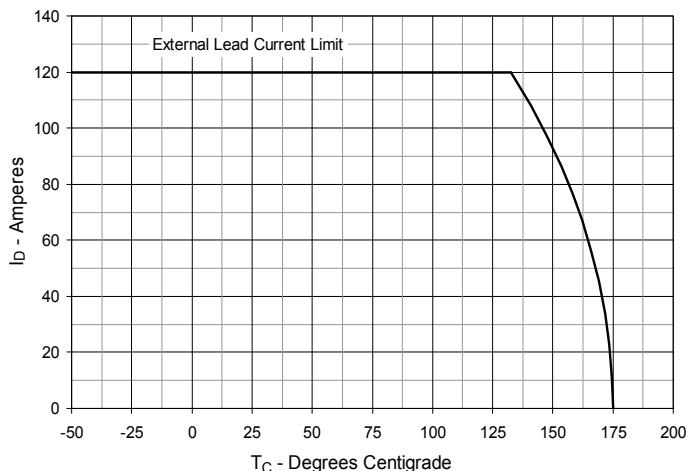
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 115\text{A}$  Value vs. Junction Temperature**

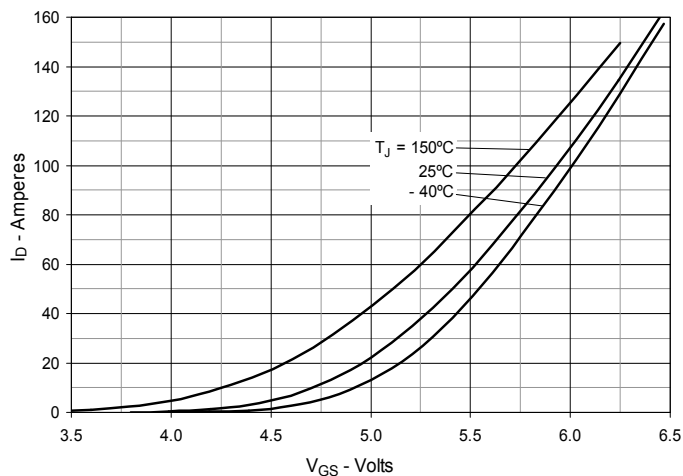
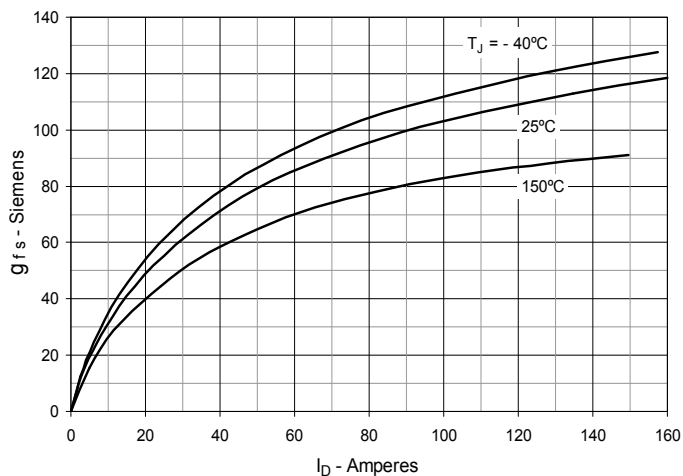
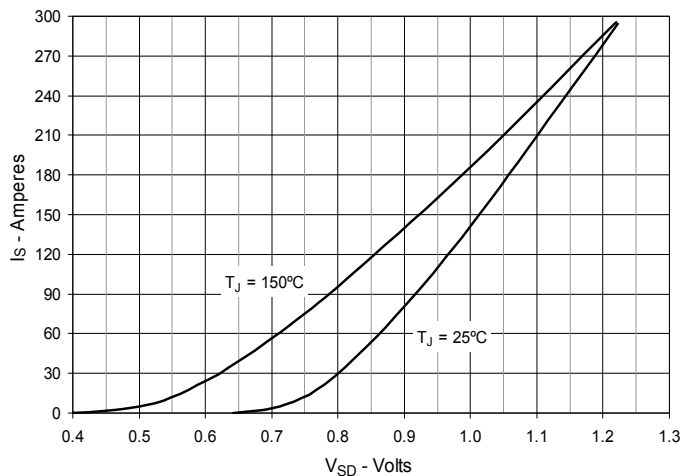
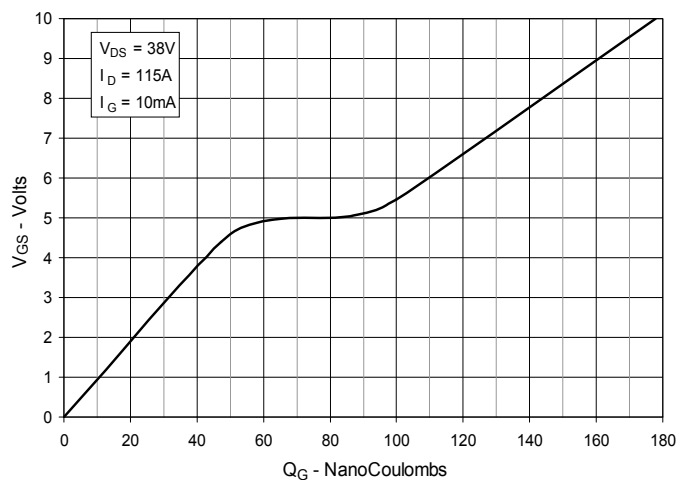
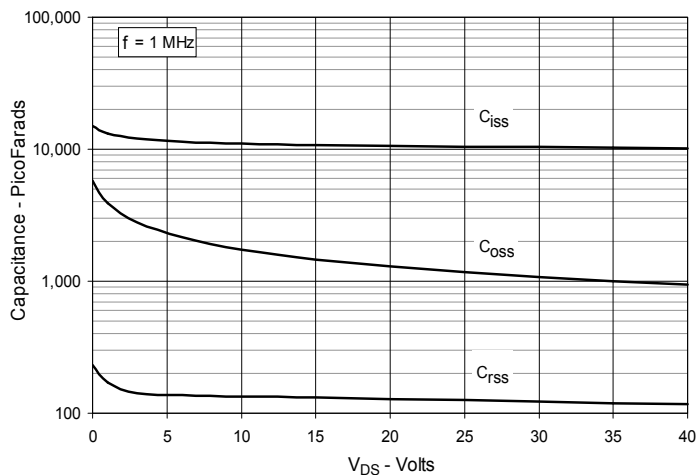
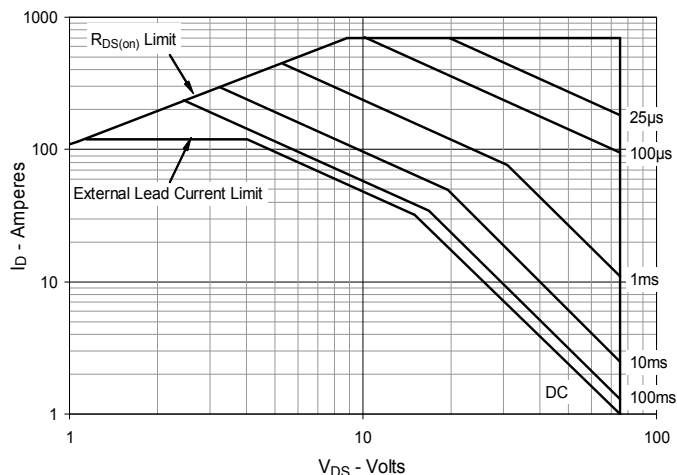


**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 115\text{A}$  Value vs. Drain Current**

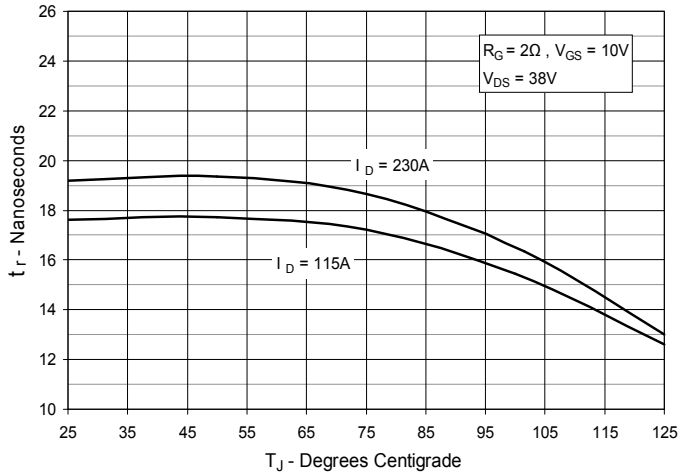


**Fig. 6. Drain Current vs. Case Temperature**

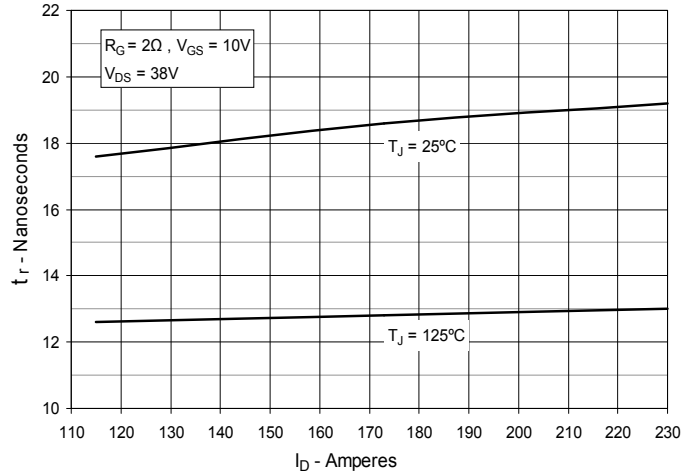


**Fig. 7. Input Admittance**

**Fig. 8. Transconductance**

**Fig. 9. Forward Voltage Drop of Intrinsic Diode**

**Fig. 10. Gate Charge**

**Fig. 11. Capacitance**

**Fig. 12. Forward-Bias Safe Operating Area**


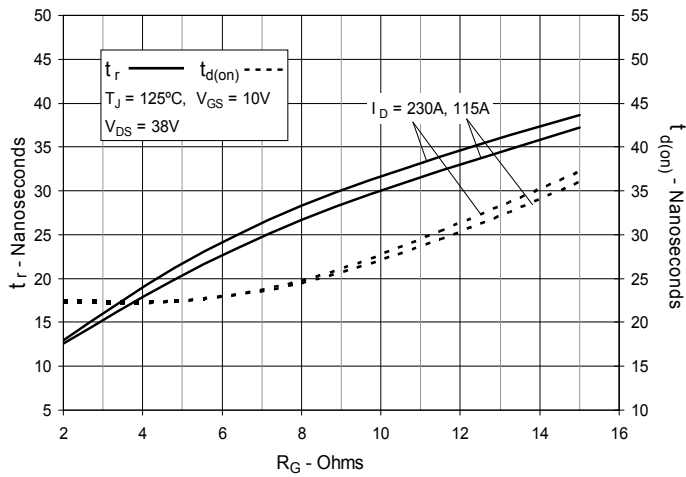
**Fig. 13. Resistive Turn-on Rise Time vs. Junction Temperature**



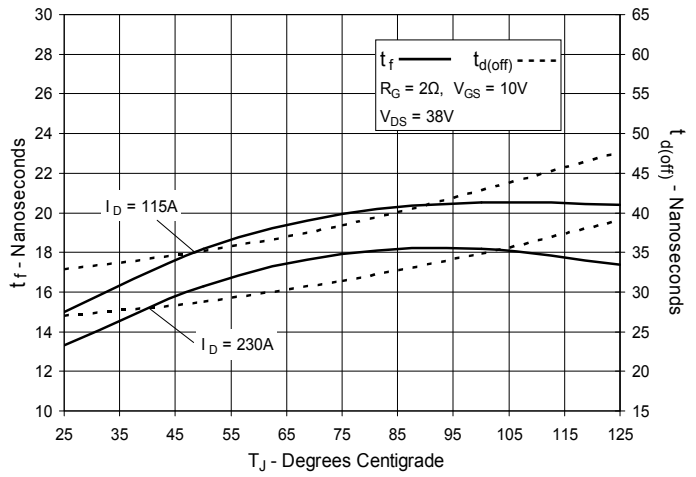
**Fig. 14. Resistive Turn-on Rise Time vs. Drain Current**



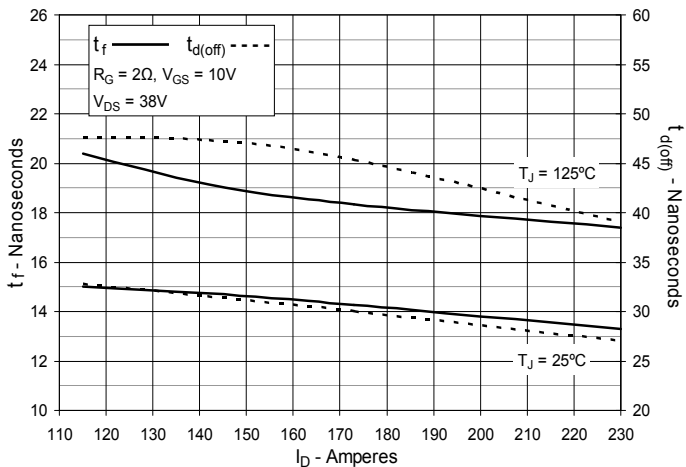
**Fig. 15. Resistive Turn-on Switching Times vs. Gate Resistance**



**Fig. 16. Resistive Turn-off Switching Times vs. Junction Temperature**



**Fig. 17. Resistive Turn-off Switching Times vs. Drain Current**



**Fig. 18. Resistive Turn-off Switching Times vs. Gate Resistance**

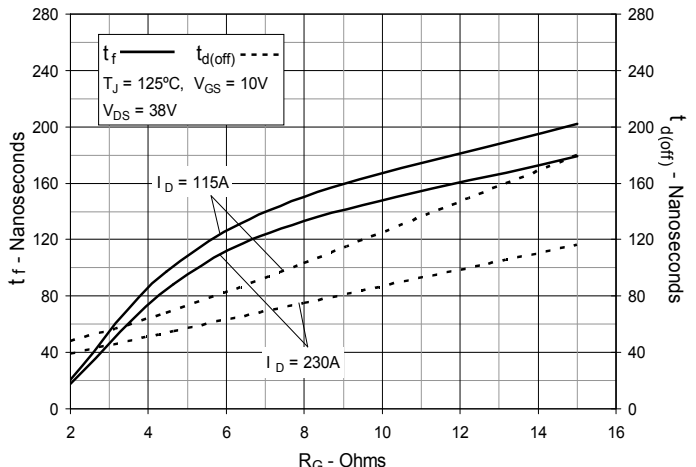


Fig. 19. Maximum Transient Thermal Impedance

